

## ABSTRACT OF THE DISCLOSURE

A semiconductor light emitting device with improved luminous efficiency is provided. An underlying n-type GaN layer is grown on a sapphire substrate, and a growth mask made from SiO<sub>2</sub> film or the like is formed on the underlying n-type GaN layer. An n-type GaN layer having a hexagonal pyramid shape is selectively grown on a portion, exposed from an opening of the growth mask, of the underlying n-type GaN layer. The growth mask is removed by etching, and then an active layer and a p-type GaN layer are sequentially grown on the entire substrate so as to cover the hexagonal pyramid shaped n-type GaN layer, to form a light emitting device. An n-side electrode and a p-side electrode are then formed.